



#### 30V N-Channel Enhancement Mode MOSFET

Voltage 30 V Current 300mA

#### **Features**

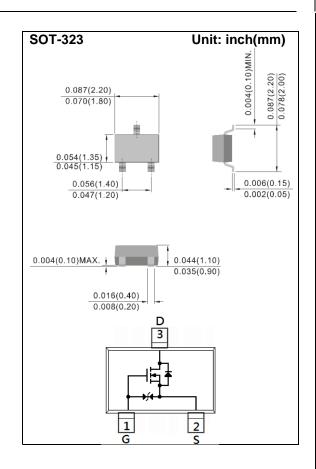
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Relay driver, Speed line drive, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC61249 standard

#### **Mechanical Data**

• Case: SOT-323 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.00018 ounces, 0.005 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	30	V	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 10		
Continuous Drain Current (Note 4)		I <sub>D</sub>	300	mA	
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	600		
Power Dissipation	T <sub>A</sub> =25°C	P <sub>D</sub>	350	mW	
	Derate above 25°C		2.8	mW/°C	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient (Note 3,4)		$R_{ heta JA}$	357	°C/W	





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.4	0.75	1		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =300mA	-	0.7	1.2	Ω	
		$V_{GS}$ =2.5V, $I_{D}$ =200mA	-	0.8	1.6		
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =100mA	-	0.9	2		
		V <sub>GS</sub> =1.5V, I <sub>D</sub> =50mA	-	1.1	3		
		V <sub>GS</sub> =1.2V, I <sub>D</sub> =20mA	-	1.5	4		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{GS}=\underline{+}8V, V_{DS}=0V$	-	-	<u>+</u> 10		
Dynamic (Note 5)							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =300mA, V <sub>GS</sub> =4.5V	-	0.9	-	nC	
Gate-Source Charge	$Q_gs$		-	0.3	-		
Gate-Drain Charge	$Q_gd$		-	0.2	-		
Input Capacitance	Ciss	$V_{DS}$ =10V, $V_{GS}$ =0V, $f$ =1MHZ	-	45	-	pF	
Output Capacitance	Coss		-	14	-		
Reverse Transfer Capacitance	Crss		-	0.8	-		
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =10V, $I_{D}$ =300mA, $V_{GS}$ =4V, $R_{G}$ =10 $\Omega$ (Note 1,2)	-	8.3	-	ns	
Turn-On Rise Time	tr		-	5.7	-		
Turn-Off Delay Time	td <sub>(off)</sub>		-	35	-		
Turn-Off Fall Time	tf		-	12	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	1		_	_	300	mA	
Diode Forward Current	I <sub>S</sub>				300	ША	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =300mA, V <sub>GS</sub> =0V	-	0.9	1.3	V	

#### NOTES:

- 1. Pulse width $\leq$ 300us, Duty cycle $\leq$ 2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.





#### TYPICAL CHARACTERISTIC CURVES

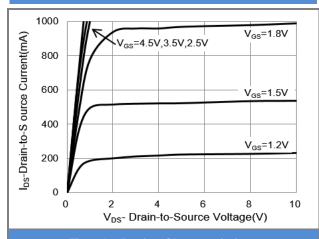
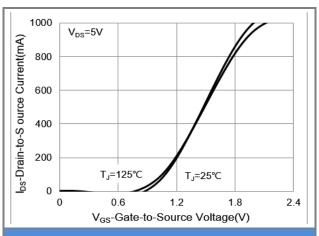


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

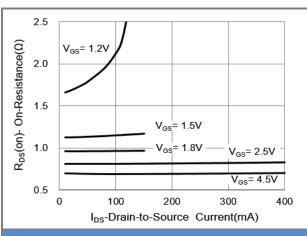


Fig.3 On-Resistance vs. Drain Current

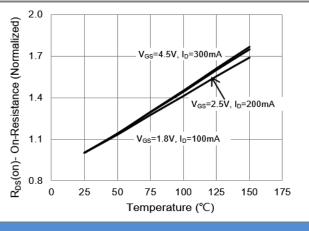
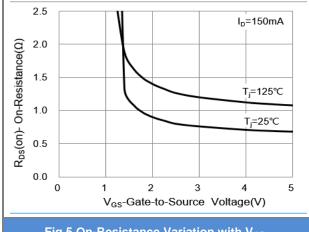


Fig.4 On-Resistance vs. Junction temperature





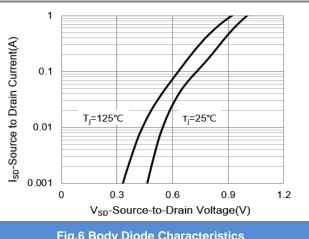


Fig.6 Body Diode Characteristics





#### **TYPICAL CHARACTERISTIC CURVES**

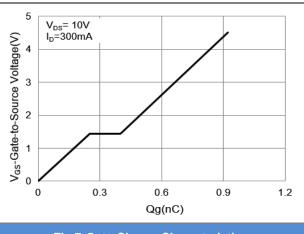


Fig.7 Gate-Charge Characteristics

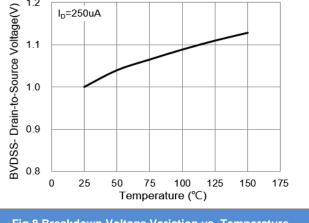


Fig.8 Breakdown Voltage Variation vs. Temperature

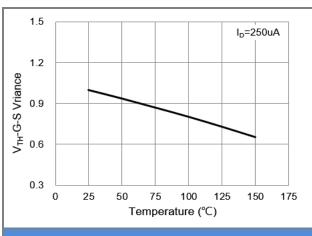


Fig.9 Threshold Voltage Variation with Temperature

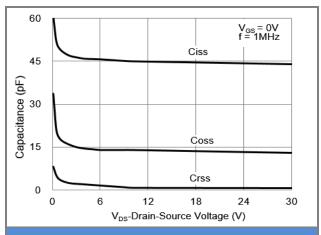


Fig.10 Capacitance vs. Drain-Source Voltage

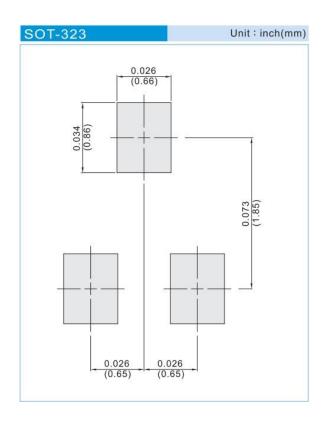




### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJC7428_R1_00001	SOT-323	3K pcs / 7" reel	C28	Halogen free

### **Mounting Pad Layout**







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